

Switchmode **Dual Ultrafast Power Rectifiers**

Designed for use in switching power supplies inverters and as free wheeling diodes. These state-of-the-art devices have the following

Features

- * High Surge Capacity
- *Low Power Loss, High efficiency
- *150 °C Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction
- *Low Forward Voltage, High Current Capability
- * High-Switching Speed 50 Nanosecond Recovery Time
- * Plastic Material used Carries Underwriters Laboratory
- * Flammability Classification 94V-O

* Pb free

* In compliance with EU RoHs directives

MAXIMUM RATINGS

Characteristic	Symbol	UE16C60C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	600	V
RMS Reverse Voltage	V _{R(RMS)}	420	V
Average Rectifier Forward Current (per diode) Total Device (Rated V _R)	I _{F(AV)}	8 16	A
Peak Repetitive Forward Current (Rate V _R , Square Wave, 20kHz)	I _{FM}	16	А
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware, single phase, 60Hz)	I _{FSM}	100	A
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

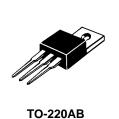
ELECTRICAL CHARACTERISTICS

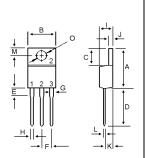
Characteristic	Symbol	Min.	Тур.	Max.	Unit
Maximum Instantaneous Forward Voltage ($I_F = 8.0 \text{ Amp } T_C = 25^{\circ}C$) ($I_F = 8.0 \text{ Amp } T_C = 125^{\circ}C$)	V _F		1.30 1.10	1.60 	V
Maximum Instantaneous Reverse Current (Rated DC Voltage, T _C = 25℃) (Rated DC Voltage, T _C = 125℃)	I _R		0.01 5	10 	uA
Reverse Recovery Time ($I_F = 0.5 A$, $I_R = 1.0$, $I_{rr} = 0.25 A$)	Trr		24	50	ns
Typical Thermal Resistance junction to case	$R_{ extsf{ heta}_{jc}}$		3.5		°C/w
Typical Junction Capacitance (Reverse Voltage of 4 volts & f=1 MHz)	CP		29		₽F

UE16C60C

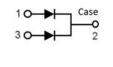
ULTRA FAST RECTIFIERS

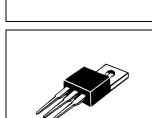
16 AMPERES 600 VOLTS





DIM	MILLIMETERS				
Divi	MIN	MAX			
Α	14.68	16.00			
В	9.78	10.42			
С	5.02	6.60			
D	13.00	14.62			
Е	3.10	4.19			
F	2.41	2.67			
G	1.10	1.67			
Н	0.69	1.01			
1	4.22	4.98			
J	1.14	1.40			
К	2.20	3.30			
L	0.28	0.61			
М	2.48	3.00			
0	3.50	4.00			





RA-D-0925 Ver.B



UE16C60C

FIG-3 FORWARD CURRENT DERATING CURVE

100

125

150

16

12

8

4

0

80

25

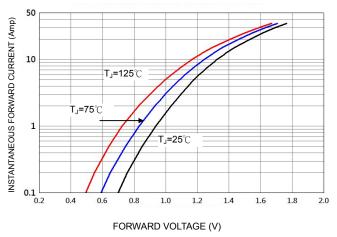
50

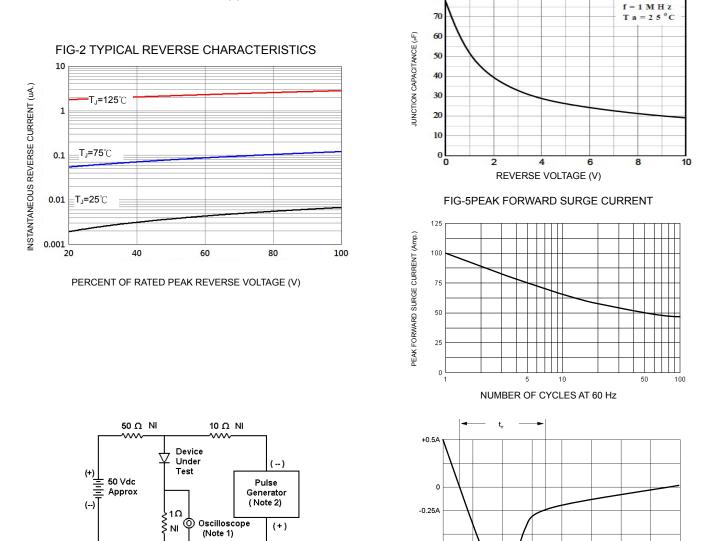
75 LEAD TEMPERATURE (°C)

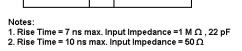
FIG-4TYPICAL JUNCTION CAPACITANCE

AVERAGE FORWARD RECTIFIED CURRENT (Amp.)

FIG-1 TYPICAL FORWARD CHARACTERISTICS







Set time base for 10/20 ns/cm

FIG-6 Reverse Recovery Time Characteristic and Test Circuit Diagram

-1.0A



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